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捷多邦, 专业PCB打样工厂, 24小时

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Microsemi Corp.

The diode experts

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(602) 941-6300

1N2804 thru
1N2846B
and
1N4557B thru
1N4564B

FEATURES

- ZENER VOLTAGE 3.9V to 200V
- AVAILABLE IN TOLERANCES OF $\pm 5\%$, $\pm 10\%$ and $\pm 20\%$
- DESIGNED FOR MILITARY ENVIRONMENTS (See Below)

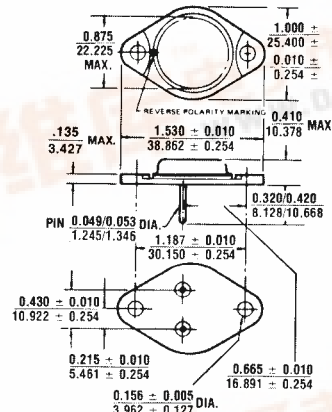
MAXIMUM RATINGS

Junction and Storage Temperatures: -65°C to $+175^{\circ}\text{C}$
DC Power Dissipation: 50 watts
Power Derating: 0.5W/ $^{\circ}\text{C}$ above 75°C
Forward Voltage @ 10 A: 1.5 Volts

*ELECTRICAL CHARACTERISTICS @ 25°C

JEDEC TYPE NO. (Note 1)	NOMINAL ZENER VOLTAGE V. @ I _Z Volts (Note 2)	ZENER TEST CURRENT (I _Z) mA	MAX. ZENER IMPEDANCE (Note 3)		MAX. DC ZENER CURRENT (I _{ZM}) @ 75°C Case Temp. mA (Note 4)	TYPICAL ZENER VOLTAGE Temp. Coeff. %/ $^{\circ}\text{C}$	MAXIMUM LEAKAGE CURRENT ** I _R @ V _R V	
			Z ₀ @ I _{Z0} OHMS	Z ₅ @ 5 mA (I _{Z5}) OHMS			μA	V
†1N4557B	3.9	3200	0.16	400	11,900	-0.046	150	0.5
†1N4558B	4.3	2900	0.16	500	10,650	-0.033	150	0.5
†1N4559B	4.7	2650	0.12	600	9,700	-0.015	100	1
†1N4560B	5.1	2450	0.12	650	8,900	± 0.010	20	1
†1N4561B	5.6	2250	0.12	900	8,100	+0.03	20	1
†1N4562B	6.2	2000	0.14	1000	7,300	+0.049	20	2
1N4563B	6.8	1850	0.16	200	6,650	+0.053	10	2
1N4564B	7.5	1650	0.24	100	6,050	+0.057	10	3
†1N2804B	6.8	1850	0.2	70	7,400	.040	150	4.5
†1N2805B	7.5	1700	0.3	70	6,600	.045	100	5
†1N2806B	8.2	1500	0.4	70	5,800	.048	50	5.4
†1N2807B	9.1	1370	0.5	70	5,300	.050	25	6.1
†1N2808B	10	1200	0.6	80	4,800	.055	25	6.7
†1N2809B	11	1100	0.8	80	4,300	.060	10	8.4
†1N2810B	12	1000	1.0	80	4,000	.065	10	9.1
†1N2811B	13	960	1.1	80	3,700	.065	10	9.9
1N2812B	14	890	1.2	80	3,400	.070	10	10.6
†1N2813B	15	830	1.4	80	3,100	.070	10	11.4
†1N2814B	16	780	1.6	80	2,950	.070	10	12.2
†1N2815B	17	740	1.8	80	2,750	.075	10	13.0
†1N2816B	18	700	2.0	80	2,550	.075	10	13.7
†1N2817B	19	660	2.2	80	2,450	.075	10	14.4
†1N2818B	20	630	2.4	80	2,350	.075	10	15.2
†1N2819B	22	570	2.5	80	2,100	.080	10	16.7
†1N2820B	24	520	2.6	80	1,950	.080	10	18.2
1N2821B	25	500	2.7	90	1,850	.080	10	19
†1N2822B	27	460	2.8	90	1,650	.085	10	20.6
†1N2823B	30	420	3.0	90	1,550	.085	10	22.8
†1N2824B	33	380	3.2	90	1,450	.085	10	25.1
†1N2825B	36	350	3.5	90	1,300	.085	10	27.4
†1N2826B	39	320	4.0	90	1,175	.090	10	29.7
†1N2827B	43	290	4.5	90	1,075	.090	10	32.7
1N2828B	45	280	4.5	100	1,030	.090	10	34.2
†1N2829B	47	270	5.0	100	980	.090	10	35.8
1N2830B	50	250	5.0	100	935	.090	10	38
†1N2831B	51	245	5.2	100	925	.090	10	38.8
†1N2832B	56	220	6	110	825	.090	10	42.6
†1N2833B	62	200	7	120	735	.090	10	47.1
†1N2834B	68	180	8	140	670	.090	10	51.7
†1N2835B	75	170	9	150	600	.090	10	56
†1N2836B	82	150	11	160	550	.090	10	62.2
†1N2837B	91	140	15	180	470	.090	10	69.2
†1N2838B	100	120	20	200	450	.090	10	76
†1N2839B	105	120	25	210	430	.095	10	79.8
†1N2840B	110	110	30	220	410	.095	10	83.6
†1N2841B	120	100	40	240	375	.095	10	91.2
†1N2842B	130	95	50	275	345	.095	10	98.8
†1N2843B	150	85	75	400	300	.095	10	114.0
†1N2844B	160	80	80	420	285	.095	10	121.6
†1N2845B	180	68	90	525	250	.095	10	136.8

SILICON
50 WATT
ZENER DIODES



All dimensions in INCH m.m. FIGURE 1

MECHANICAL CHARACTERISTICS

CASE: Industry Standard TO-3, (modified), hermetically sealed, 0.052 inch diameter pins.

FINISH: All external surfaces are corrosion resistant and terminal solderable.

THERMAL RESISTANCE: 1.5 $^{\circ}\text{C}/\text{W}$ (Typical) junction to base.

POLARITY: Standard Polarity units are connected anode to case. Reverse polarity (cathode to case is indicated by a red dot on the base plate. (Suffix R)

WEIGHT: 15 grams.

MOUNTING HARDWARE: See page 2-9.

1N2804 thru 1N2846B, 1N4557B thru 1N4564B

NOTE 1 The JEDEC type numbers shown (B suffix) have a $\pm 5\%$ tolerance on nominal zener voltage. The suffix A is used to identify $\pm 10\%$ tolerance; no suffix indicates $\pm 20\%$ tolerance. If tighter tolerance is required, consult factory. Standard polarity units have the anode connected to the case. Reverse polarity (cathode-to-case) units are available and are indicated by suffixing an R to the part number.

NOTE 2 Zener Voltage (V_Z) is measured with junction in thermal equilibrium with 30°C base temperature. The test currents (I_{ZT}) have been selected so that at nominal voltages the dissipation is a constant 12.5 watts. This results in a nominal junction temperature rise of 18.75°C .

NOTE 3 The zener impedance is derived from the 60 cycle A.C. voltage, which results when an A.C. current having an R.M.S. value equal to 10% of the D.C. zener current (I_{ZT} or I_{ZK}) is superimposed on I_{ZT} or I_{ZK} . Zener impedance is measured at 2 points to insure a sharp knee on the breakdown curve and to eliminate unstable units. A curve showing the variation of zener impedance vs. zener current for six representative types is shown in Figure 3. A 100% cathode ray tube curve trace test is used to insure that each zener diode breakdown region begins at a current lower than I_{ZK} and continues at nearly constant voltage to a current level in excess of I_{ZM} .

NOTE 4 The values of I_{ZM} are calculated for a $\pm 5\%$ tolerance on nominal zener voltage. Allowance has been made for the rise in zener voltage above V_{ZT} which results from zener impedance and the increase in junction temperature as power dissipation approaches 50 watts. In the case of individual diodes I_{ZM} is that value of current which results in a dissipation of 50 watts.

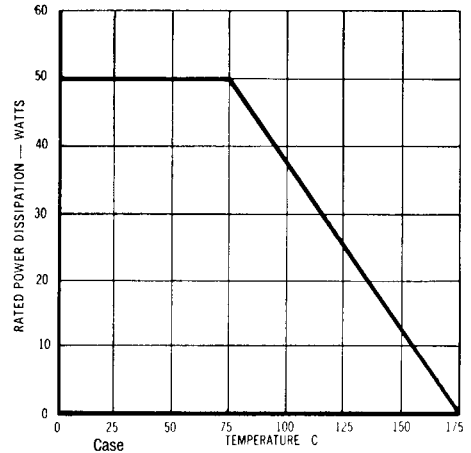
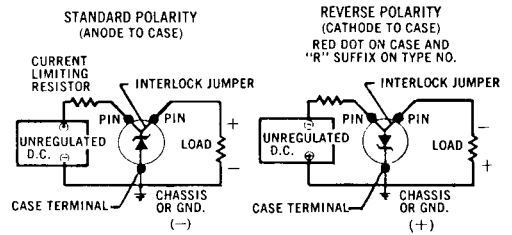


FIGURE 2
POWER DERATING CURVE



Typical circuit connections for anode-to-case and cathode-to-case polarities (standard and reverse polarities, respectively).

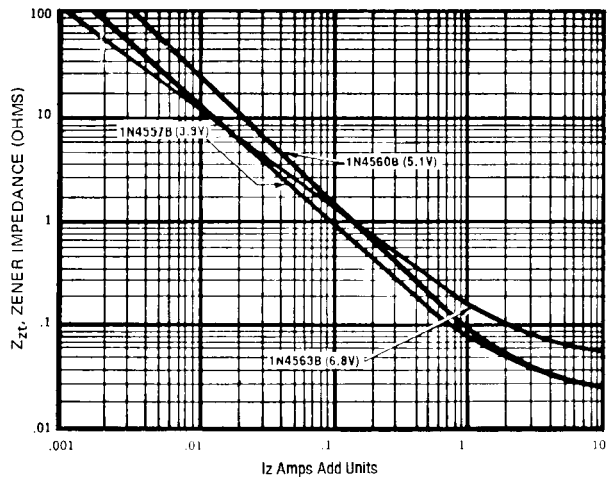
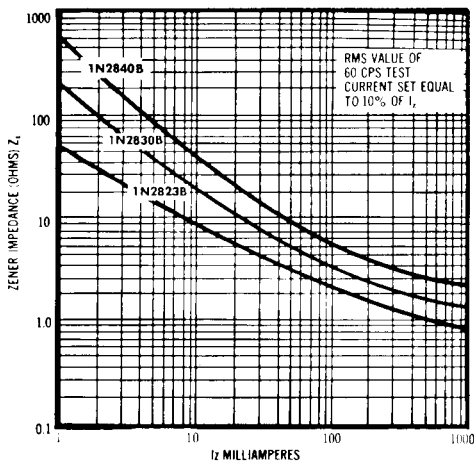


FIGURE 3

TYPICAL ZENER IMPEDANCE vs. ZENER CURRENT